Journal of Materials Chemistry C

Accepted Manuscript



This is an *Accepted Manuscript*, which has been through the Royal Society of Chemistry peer review process and has been accepted for publication.

Accepted Manuscripts are published online shortly after acceptance, before technical editing, formatting and proof reading. Using this free service, authors can make their results available to the community, in citable form, before we publish the edited article. We will replace this Accepted Manuscript with the edited and formatted Advance Article as soon as it is available.

You can find more information about *Accepted Manuscripts* in the **Information for Authors**.

Please note that technical editing may introduce minor changes to the text and/or graphics, which may alter content. The journal's standard <u>Terms & Conditions</u> and the <u>Ethical guidelines</u> still apply. In no event shall the Royal Society of Chemistry be held responsible for any errors or omissions in this *Accepted Manuscript* or any consequences arising from the use of any information it contains.



www.rsc.org/materialsC

Journal Name

COMMUNICATION

Synthesis of $Na_2SiF_6:Mn^{4+}$ red phosphors for white LED applications by co-precipitation[†]

Cite this: DOI: 10.1039/x0xx00000x

Hoang-Duy Nguyen,^{ab‡} Chun Che Lin,^{a‡} Mu-Huai Fang^a and Ru-Shi Liu^{*ac}

Received 00th January 2012, Accepted 00th January 2012

DOI: 10.1039/x0xx00000x

www.rsc.org/

A one-step approach to synthesize Na₂SiF₆:Mn⁴⁺and K₂SiF₆:Mn⁴⁺ red phosphors by co-precipitation are reported in this paper. The phosphors were precipitated from a silicon fluoride solution with NaF and Na₂MnO₄ (Na₂SiF₆:Mn⁴⁺ preparation) or KF and K_2MnO_4 ($K_2SiF_6:Mn^{4+}$ preparation) using H_2O_2 to reduce Mn^{7+} to Mn⁴⁺ at room temperature. Na₂SiF₆:Mn⁴⁺ was also prepared through a convenient two-step route with K₂MnF₆ as raw material. The obtained Na₂SiF₆:Mn⁴⁺ phosphors have hexagonal structure with space group $D_2^2 - P321$ and no impurity phase when were examined via X-ray diffraction. Photoluminescence, photoluminescence excitation, thermal luminescence, and luminescence decay time were considered to determine the optical properties of the fluoride complexes. The prepared phosphors exhibited bright red emission under 460 nm light excitation and low-thermal quenching (~92% of the luminescent intensity at 423 K). Increasing the concentration of Mn⁴⁺ enhanced luminescence intensity. A warm white light LED with high color rendering index ($R_a = 86$ and R9 = 61) was fabricated by employing Na₂SiF₆:Mn⁴⁺ as red phosphor and commercial Y₃Al₅O₁₂:Ce³⁺ yellow phosphor on a blue-InGaN chip.

^aDepartment of Chemistry, National Taiwan University, Taipei 106, Taiwan. E-mail:rsliu@ntu.edu.tw

^bInstitute of Applied Material Science, Vietnam Academy of Science and Technology, Hochiminh City, Vietnam

^cDepartment of Mechanical Engineering and Graduate Institute of Manufacturing Technology, National Taipei University of Technology, Taipei 106, Taiwan

^tH.-D. Nguyen and C. C. Lin contributed equally

†Electronic Supplementary Information (ESI) available: [details of any supplementary information available should be included here]. See DOI: 10.1039/c000000x/

1. Introduction

White light-emitting diodes (WLEDs) have attracted much attention because of their energy-saving and environment-friendly characteristics.^{1,2} Most commercial WLEDs are based on the combination of blue LED chips and yellow-emitting YAG:Ce³⁺ phosphors.^{2–5} However, such approach limits the application range to cool white light (correlated color temperature of 4.000 K - 8.000 K) and limits the color rendering index $(CRI < 75)^{6,7}$ because of the lack of red emission in the luminescent spectra. The use of rare-earthactivated sulfide,^{10,11} molybdates/tungstate,¹² and nitride¹³⁻¹⁵ red phosphors have been proposed to fabricate warm WLEDs with high color-rendering index (CRI, R_a > 80) and low correlated color temperatures (2,700 K - 4,000 K).⁷⁻⁹ However, these materials have drawbacks. Although they possess attractive luminescence, sulfide phosphors strongly quench emission with temperature and are highly sensitive toward hydrolysis because of their rather ionic nature of binary sulfides. High color rendering index was observed for Eu³⁺activated phosphors, but they have low absorption in blue or near-UV light, which can be attributed to the parity-forbidden 4f-4f transitions. Although nitride phosphors are commercially applied because of their sufficient chemical strength and efficient luminescence, their broad emission bands greatly limit the maximum achievable luminous efficacies of high-quality warm WLEDs.^{9,16}

Recent studies have focused on the preparation of narrow-band red-emitting fluoride phosphors doped by manganese (IV) (Mn⁴⁺) because of their good thermal stability and potential application in solid-state light sources. The valence states of Mn (2+, 3+, 4+, 6+ and 7+) are sensitive to the synthesis temperature. Hence, the main difficulty lies in controlling the Mn valence state for synthesizing Mn⁴⁺-activated fluoride complexes. Adachia et al. prepared a series of red fluoride phosphors, $A_2MF_6:Mn^{4+}$ (A = K, Na, Cs, or NH₄; M = Si, Ge, Zr, Sn, or Ti) and $BSiF_6:Mn^{4+}$ (B = Ba or Zn), via wet chemical etching of silicon wafers in aqueous HF solution with the addition of oxidizing agent KMnO₄ at room temperature.¹⁷⁻²⁶ The fluoride complexes have broad, intensive absorption in the longwavelength region, which complements the electroluminescence of commercial blue LEDs, and generate highly efficient red light. However, the technique has significant drawbacks, namely, expensive pure Si wafers and metal shots used during synthesis, prolonged reaction time, tedious post treatment, and low yield.

Convenient synthesis methods and the photoluminescence properties of fluoride phosphors have received much attention. Fluoride red phosphors - K2TiF6:Mn4+, K2SiF6:Mn4+ prepared through cation exchange reaction by mixing fluoride hosts with HF solution dissolved with K₂MnF₆ powders at room temperature in 20 minutes; K₂SiF₆:Mn⁴⁺ prepared via redox reaction in HF/KMnO₄ solution at room temperature in 10 minutes; K₂SiF₆:Mn⁴⁺, BaTiF₆:Mn⁴⁺ and BaSiF₆:Mn⁴⁺ prepared by hydrothermal method at 120 °C in 12–20 h – have shown high emission efficiency.^{27–31} However, these feasible approaches could not apply for preparing all kinds of fluoride phosphor, Na₂SiF₆:Mn⁴⁺ is an example. Therefore, a simple co-precipitation method to synthesize Na₂SiF₆:Mn⁴⁺ and K₂SiF₆:Mn⁴⁺ is presented in this paper. The prepared phosphor powders, which could be used for commercial application, exhibited efficient emission intensity, high color purity, and excellent thermal stability. Silicon oxide is easily dissolved in a concentrated HF solution. Thus, chemical co-precipitation of Na^+ and SiF_6^{4-} can be performed in HF/NaMnO₄ solution using H₂O₂ to efficiently reduce Mn^{7+} to Mn^{4+} at room temperature in a few minutes, which is suitable for quantifiable production because of its high yield, good repeatability, and low cost. Na2SiF6:Mn4+ was also synthesized through a two-step co-precipitation method in which K₂MnF₆, prepared from a silicon fluoride solution in the presence of KMnO₄ and H₂O₂, was used as a starting material. The effect of K2MnF6 concentration on the luminescent intensity of Na2SiF6:Mn4+ was determined. The prepared fluoride red phosphors are potential candidates for warm WLED applications.

2. Experimental

One-step approach: Na₂SiF₆:Mn⁴⁺ (NSFM-1S) was synthesized through a simple one-step method (Fig. 1). Silicon fluoride solution was formed by dissolving 1.2 g SiO₂ powders in 25 mL 48% HF solution at 60 °C for 2 h. The solution was cooled to room temperature and separated from residual powder using filter paper. Solution A was formed by adding 1.84 g NaMnO₄.H₂O to the filtered solution. Thereafter, a saturated NaOH (1.6 g NaOH in 15 mL 48% HF) or Na₂CO₃ (1.6 g Na₂CO₃ in 15 mL 48% HF) or Na₂SO₄ (3.0 g Na₂SO₄ in 15 mL 48% HF) solution containing 1.0 mL H_2O_2 (35% – 40%) was added to solution A under vigorous stirring. The deep purple solution rapidly turned to pale orange. The powder was obtained as 100 mL acetone (99.9%) was poured into the resulting solution. The powder was dried at 70 °C after washing with 20% HF solution to remove undesired products and residual chemicals, and then washed several times with ethanol (99.9%).

 $K_2SiF_6:Mn^{4+}$ (KSFM-1S) was also prepared following the one-step method, but KMnO₄ and KF, instead of NaMnO₄ and NaOH, were used (The structure and luminescent properties of KSFM-1S are shown in Supplementary Figs. S3–S6).

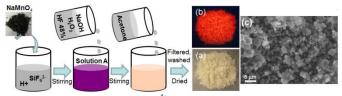


Fig. 1 Synthesis of Na₂SiF₆:Mn⁴⁺ red phosphor via one-step method, and digital images of Na₂SiF₆:Mn⁴⁺ under (a) warm room light and (b) UV light ($\lambda_{ex} = 365$ nm) excitation; (c) Scanning electron micrographs of NSFM-1S.

Journal Name

Page 2 of 5

Two-step approach: K₂MnF₆ was used as raw material for the two-step synthesis of Na₂SiF₆:Mn⁴⁺ (NSFM-2S) phosphor (Fig. 2). For K₂MnF₆ preparation, a mixture, which consisted of 9.0 g KHF₂ and 0.45 g KMnO₄, was dissolved in 30 mL solution of 48% HF. Then, 0.3 mL $H_2O_2(35\% - 40\%)$ was added to the solution using a dropper. The deep purple solution gradually turned yellow, and a yellow precipitate was obtained. The powder was washed with acetone several times and dried at 70 °C for 2 h. K₂MnF₆ product was identified via X-ray powder diffraction (XRD; D2PHASER:Cu- $K\alpha$ radiation, Bruker AXS, Germany; Supplementary Fig. S7) before it was used for $Na_2SiF_6{:}Mn^{4+}$ synthesis. The prepared K_2MnF_6 powder (0.05 g - 0.30 g) was dissolved in the silicon fluoride solution (1.2 g SiO₂ and 25 mL 48% HF) while stirring. Then, 4.2 g Na_2SO_4 was added slowly to the solution for 3 min – 5 min while stirring for 15 min. Yellow powder was obtained and washed with 20% HF solution, washed twice with ethanol (99.9%), and dried at 70 °C for 6 h.



Fig. 2 Synthesis of Na₂SiF₆:Mn⁴⁺ red phosphor via two-step method, and digital images of Na₂SiF₆:Mn⁴⁺ under (a) warm light and (b) UV light ($\lambda_{ex} = 365$ nm) excitation; (c) Scanning electron micrographs of NSFM-2S.

The prepared NSFM-1S and NSFM-2S samples show a uniform pale yellow tint under warm light illumination (Figs. 1a and 2a), and generate bright red light under 365 nm illumination (Figs. 1b and 2b). The scanning electron micrographs of $Na_2SiF_6:Mn^{4+}$ red phosphor show Na_2SiF_6 near round-like crystals prepared via both methods (Figs. 1c and 2c). The particle size was primarily in the range of 1 μ m – 5 μ m for NSFM-1S and 5 μ m – 10 μ m for NSFM-2S.

The purity and structure of the obtained phosphors were examined via XRD. A scanning electron microscope (JEOL JSM-6700F, Japan) was used to characterize the morphology of the fluoride materials. A FluoroMax-3 spectrophotometer (HORIBA, Japan) equipped with a 150 W Xe lamp was used to measure the RT excitation and emission spectra. For temperature-dependent experiments at 303–573 K, the samples were placed in a small platinum hold with its temperature controlled by a heating THMS-600 device (Linkam Scientific Instruments Ltd., UK). Light was radiated by a Hamamatsu R928 photo-multiplier tube.

The commercial YAG: Ce^{3+} yellow phosphor, $Na_2SiF_6:Mn^{4+}$ red phosphor and blue chips (455 nm, 250 mW, 350 mA, APT Electronics Ltd., China) were used to fabricate WLEDs. The phosphors were mixed with silicone resin (Dow Corning OE-6630 A and B) thoroughly. The obtained phosphor–silicone mixture was coated on the surface of the LED chips. The photoelectric properties of the fabricated devices were measured by an integrating sphere spectroradiometer system (PMS-80, Everfine Photo-EINFO Co. Ltd., China). The LEDs were operated at 2.0 V with current of 200 mA.

3. Results and discussion

Journal Name

Synthesis strategy: H_2O_2 was used during preparation to reduce reaction time. The co-precipitation of silicon fluoride with NaF in $HF/NaMnO_4$ solution in the presence of H_2O_2 is represented as follows:

$$\begin{split} \text{NaOH} + \text{HF} &\rightarrow \text{NaF} + \text{H}_2\text{O} \\ (2-2x)\text{SiO}_2 + 2x\text{NaMnO}_4 + (4-2x)\text{NaF} + (8+2x)\text{HF} + (2-x)\text{H}_2\text{O}_2 \\ &\rightarrow 2\text{Na}_2\text{Si}_{1-x}\text{Mn}_x\text{F}_6 + 6\text{H}_2\text{O} + (1+x)\text{O}_2 \uparrow \end{split}$$

The amount of K_2MnF_6 in the two-step approach should not exceed 0.30 g to prevent undesired K_2SiF_6 precipitation. Given that the solubility of K_2SiF_6 (S_{K2SiF_6}) in 48% HF solution is 0.146 M,³² the precipitation will occur as

$$[K^+]^2 \times [SiF_2^{2^-}] \ge 4 \times (S_{K2SiF6})^3 \sim 1.24 \times 10^{-2}$$

The silicon fluoride solution used in the preparation process had a concentration of 0.8 M. Therefore, K^+ concentration in the prepared solution should be lower than 0.124 M, and K_2MnF_6 concentration should not be higher than 0.062 M (~0.38 g K_2MnF_6 in 25 mL 48% HF solution).

Na₂SiF₆:Mn⁴⁺ prepared by different methods have diverse XRD patterns and crystal structures (Fig. 3a). All diffracted peaks can be indexed to space group D_2^2 -P321 of hexagonal Na₂SiF₆ (JCPDS No. 33-1280). Neither K₂SiF₆ nor secondary phases were identified, indicating that all prepared samples have a single phase, Na₂SiF₆:Mn⁴⁺. The crystal structure of Na₂SiF₆ viewed from the [110] direction is shown in Fig. 3b. Each Si⁴⁺ is surrounded by six F⁻ to form a regular SiF₆²⁻ octahedron. Na⁺ is at the center of 12 neighboring F forming a nearly regular polyhedron.

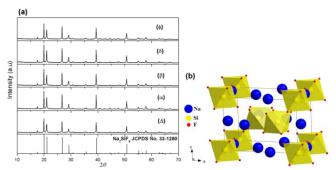


Fig. 3 (a) XRD patterns of (Δ) NSFM-1S, and NSFM-2S using (α) 0.008, (β) 0.016, (δ) 0.032, and (ϕ) 0.048 M of K₂MnF₆; (b) Crystal structure of Na₂SiF₆:Mn⁴⁺.

The photoluminescence excitation (PLE) and photoluminescence (PL) spectra of Na₂SiF₆:Mn⁴⁺ red phosphors were measured at room temperature (Fig. 4a). The emission at 620 nm ($\lambda_{em} = 620$ nm) was monitored. The excitation spectrum exhibited two broad bands with peaks at ~460 and ~360 nm, mainly because of the spin-allowed transitions of ${}^{4}A_{2g} \rightarrow {}^{4}T_{1g}$ and ${}^{4}A_{2g} \rightarrow {}^{4}T_{2g}$, respectively. The sharp red emission lines from 600 nm to 650 nm originated from the spin-forbidden ${}^{2}E_{g} \rightarrow {}^{4}A_{2g}$ transitions.^{27,33} The seven main peaks in the emission band, at ~594, 605, 609, 618, 627, 631, and 643 nm, are due to transitions of the v_3 (t_{1u}), v_4 (t_{1u}), v_6 (t_{2u}), zero phonon line (ZPL), v_6 (t_{2u}), v_4 (t_{1u}), and $v_3(t_{1u})$ vibronic modes, respectively, similar to that of Na₂SiF₆:Mn⁴⁺ prepared by wet chemical etching of Si wafer.^{18,19} ZPL emission is clearly observed in the PL spectra of Na₂SiF₆:Mn⁴⁺ hexagonal phase at room temperature, but hardly observed in that of K₂SiF₆:Mn⁴⁺ cubic phase (Fig. 4b). ZPL emission intensity is dependent on the local symmetry of the Mn⁴⁺ ion

surroundings. A Mn⁴⁺-activated material with lower crystal symmetry is expected to show higher ZPL emission intensity.¹⁹

No K₂SiF₆:Mn⁴⁺ phase could be found in Na₂SiF₆:Mn⁴⁺ samples prepared by two-step method. The luminescence intensity of Na₂SiF₆:Mn⁴⁺ increased along with the concentration of K₂MnF₆ (Fig. 4c). Red emission (627 nm) intensity of Na₂SiF₆:Mn⁴⁺ under 460 nm light excitation is a function of K₂MnF₆ concentration, and the optimum concentration of K₂MnF₆ is 0.048 M (insert in Fig. 4c). A higher concentration of K₂MnF₆ may lead to the formation of undesired potassium compounds.

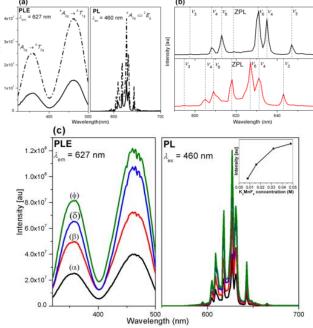


Fig. 4 (a) PLE and PL spectra of NSFM-1S (solid line) and NSFM-2S (dash-dot line); (b) PL spectra of KSFM-1S (black line) and NSFM-2S (red line); (c) PLE and PL spectra of NSFM-2S using (α) 0.008, (β) 0.016, (δ) 0.032 and (ϕ) 0.048 M of K₂MnF₆; Inserted picture shows 627 nm emission intensity as a function of K₂MnF₆ concentration under 460 nm light excitation.

Room temperature PL decay characteristics of the emitting state ${}^{2}E_{g}$ in the prepared phosphors are shown (Fig. 5). PL decay time was determined based on single exponential fit. The PL lifetimes of 4.8, 5.8, and 7.4 ms were found for NSFM-1S, NSFM-2S, and KSMF-1S, respectively. The results complement the Na₂SiF₆:Mn⁴⁺ and K₂SiF₆:Mn⁴⁺ phosphors prepared from Adachia et al.'s etching method.^{17–19}

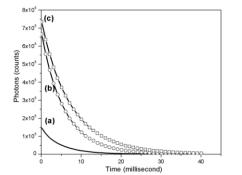


Fig. 5 PL decay curves of (a) NSFM-1S, (b) NSFM-2S, and (c) KSF-1S at 300 K.

The temperature-dependent emission spectra of Na₂SiF₆:Mn⁴⁺ phosphors under 460 nm light excitation are also presented (Fig. 6a). Increasing the temperature from 303 K to 573 K, emission lines all became broader, and the red shifted because of the increased absorbed photons and enhanced vibration transition coupling associated with the vibration modes of MnF_6^{2-} octahedron. The temperature-dependent behavior of integrated PL intensity (I_{PL}/I_{PL303}) (Fig. 6b) showed considerable stability for Na₂SiF₆:Mn⁴⁺ red phosphor in the temperature range of 303 K - 423 K. At 432 K, the relative PL intensity of the sample remained at 92% of that at 303 K, clearly showing better thermal stability than the widely-used YAG:Ce phosphor³⁴ (88% at 423 K). Non-radiative transition probability increased with temperature and integrated PL intensity showed thermal quenching, which can be fitted by $I_T/I_0 = [1 + D]$ $\exp(-E_a/kT)$]⁻¹, where I_0 is intensity at T = 0 K, and D and activation energy $E_{\rm a}$ are refined variables. The activation energies obtained for Na₂SiF₆:Mn⁴⁺ red phosphor was 0.62 eV, thrice higher than that of nitride compounds³⁵ (~ 0.23 eV), confirming the excellent thermal stability of the subject phosphors.

The performance of WLEDs fabricated by combining blue InGaN chips, commercial $Y_3Al_5O_{12}$:Ce³⁺ yellow phosphor and NSFM-2S red phosphor are evaluated for commercial applications. The sharp emission lines of Mn⁴⁺ in Na₂SiF₆ lattice are observed in electroluminescent spectra of the WLED (Fig. 6c). A luminous efficacy of 77.6 lm W⁻¹, CRI of 86 and R9 = 61 for the WLED is obtained under a drive current of 200 mA (insert image). Chromaticity coordinate (0.3126, 0.2951) laid near the black body locus in Commission Internationale de l'Éclairage (CIE) 1931 color spaces and the color temperature of 6875 K was observed for the fabricated WLEDs (Figure S8). The thermal stability and package results indicate the Na₂SiF₆:Mn⁴⁺ red phosphor as promise candidate for improving the color reproducibility of the current commercial white-LEDs.

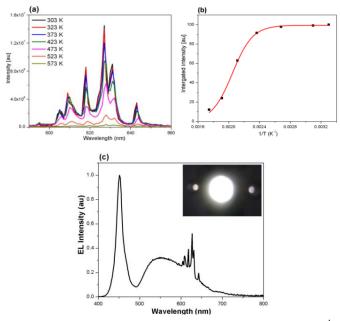


Fig. 6 (a) Temperature-dependent emission spectra of Na₂SiF₆:Mn⁴⁺; (b) Integrated red PL intensity as a function of temperature (303 K – 573 K) for NSFM-2S. The solid line represents the fitting result with the expression of $I_T/I_0 = [1 + D \exp(-E_a/kT)]^{-1}$ for NSFM-2S; (c) Luminescence spectra of the White-LEDs used Na₂SiF₆:Mn⁴⁺ red

phosphor; Inserted picture shows bright white-light emitted from the fabricated WLED.

4. Conclusions

In conclusion, red fluoride phosphors Na₂SiF₆:Mn⁴⁺ and K₂SiF₆:Mn⁴⁺ were synthesized from simple co-precipitation routes. NSFM-1S and NSFM-2S had a micrometer-size hexagonal structure. No impurities or other fluoride phases were detected in the NSFM-2S samples. The prepared phosphors had strong blue-light absorption and intense narrow-band red-emission. The luminescence intensity of NSFM-2S phosphor significantly increased when Mn⁴⁺ content was increased. The NSFM-2S phosphors exhibited excellent thermal stability with integrated PL intensity over 90% at 423 K. The important improvement in CRI (86) of WLED fabricated using red phosphor was observed. Efficient red Na₂SiF₆:Mn⁴⁺ luminescence under blue light excitation, low-thermal quenching, and a simple synthesis process qualify Na₂SiF₆:Mn⁴⁺ as a potential candidate for improving the color reproducibility of WLED.

Acknowledgements

The authors would like to thank the National Science Council of the Ministry of Science and Technology of Taiwan (Contract Nos. MOST 101-2113-M-002-014-MY3) for the financial support for this study.

References

- M. H. Chang, D. Das, P. V. Varde and M. Pecht, *Microelectron. Reliab.*, 2012, **52**, 762-782.
- 2 I. Ahemen, K. DeDilip and A.N. Amah, *Appl. Phys. Res.*, 2014, 6, 95-108.
- 3 R. Zhang, H. Lin, Y. Yu, D. Chen, J. Xu and Y. Wang, *Laser Photonics Rev.*, 2014, 8, 158-164.
- 4 H. Shi, C. Zhu, J. Huang, J. Chen, D. Chen, W. Wang, F. Wang, Y. Cao and X. Yuan, *Opt. Mat. Express*, 2014, 4, 649-655.
- 5 C. C. Lin and R.S. Liu, J. Phys. Chem. Lett., 2011, 2, 1268-1277.
- 6 P. Schlotter, R. Schmidt and J. Schneider, *Appl. Phys. A*, 1997, 64, 417-418.
- 7 P. Pust, V. Weiler, C. Hecht, A. Tücks, A. S. Wochnik, A.-K. Hen, D. Wiechert, C. Scheu, P. J. Schmidt and W. Schnick, *Nature Mater.*, 2014, **13**, 891-896.
- 8 M. R. Krames, O. B. Shchekin, R. Mueller-Mach, G. O. Mueller, L. Zhou, G. Harbers and M. G. Crafor, J. Disp. Tech., 2007, 3, 160-175.
- 9 P. F. Smet, A. B. Parmentier and D. Poelman, J. Electrochem. Soc., 2011, 158, R37-R54.
- 10 D. Poelman, J. E. V. Haecke and P. F. Smet, J. Mater. Sci.: Mater. Electron., 2009, 20, S134-S138.
- R. Mueller-Mach and G. O. Mueller, *Proceed. SPIE*, 2000, **3938**, 30-41.
- 12 P. S. Dutta and A. Khanna, ECS J. Solid State Sci. Technol., 2013, 2, R3153-R3167.
- 13 R.-J. Xie, N. Hirosaki, K. Sakuma and N. Kimura, J. Phys. D: Appl. Phys., 2008, 41, 144013 1-6.
- 14 H. Nersisyan, H. I. Won and C. W. Won, *Chem. Commun.*, 2011, 47, 11897-11899.
- 15 K. Uheda, N. Hirosaki, Y. Yamamoto, A. Naito, T. Nakajima and H. Yamamoto, *Electrochem. Solid State Lett.*, 2006, 9, H22-H25.
- 16 N. C. George, K. A. Denault and R. Seshadri, Annu. Rev. Mater. Res., 2013, 43, 481-501.

Journal Name

- 17 T. Takahashi and S. Adachi, J. Electrochem. Soc., 2008, 155, E183-E188.
- 18 S. Adachi, H. Abe, R. Kasa and T. Arai, J. Electrochem. Soc., 2012, 159, J34-J37.
- 19 Y. K. Xu and S. Adachi, J. Appl. Phys., 2009,105, 013525 1-6.
- 20 Y. Arai and S. Adachi, J. Lumin., 2011, 131, 2652-2660.
- 21 R. Kasa and S. Adachi, J. Appl. Phys. 2012, 112, 013506 1-6.
- 22 Y. Arai, T. Takahashi and S. Adachi, Opt. Mat., 2010, 32, 1095-1101.
- 23 Y. K. Xu and S. Adachi, J. Electrochem. Soc., 2011, 158, J58-J65.
- 24 Y. K. Xu and S. Adachi, J. Electrochem. Soc., 2012, 159, E11-E17.
- 25 D. Sekiguchi, J. Nara, S. Adachi, J. Appl. Phys. 2013, 113, 183516 16.
- 26 R. Hoshino and S. Adachi, J. Appl. Phys., 2013, 114, 213502 1-6.
- 27 H. M. Zhu, C. C. Lin, W. Luo, S. T. Shu, Z. G. Liu, M. Wang, J. T. Kong, E. Ma, Y. Cao, R. S. Liu and X. Y. Chen, *Nat. Commun.*, 2014, 5, 4312 1-10.
- 28 C. Liao, R. Cao, Z. Ma, Y. Li, G. Dong, K. N. Sharafudeen and J. Qiu, J. Am. Ceram. Soc., 2013, 96, 3552-3556.
- 29 X. Jiang, Y. Pan, S. Huang, X. Chen, J. Wang and G. Liu, J. Mater. Chem. C, 2014, 2, 2301-2306.
- 30 X. Jiang, Z. Chen, S. Huang, J. Wang and Y. Pan, *Dalton Trans.*, 2014, 43, 9414-9418.
- 31 L. Lv, X. Jiang, S. Huang, X. Chen and Y. Pan, J. Mater. Chem. C, 2014, 2, 3879-3884.
- 32 J. Frayret, A. Castetbon, G. Trouve and M. Potin-Gautier, *Chem. Phys. Lett.*, 2006, **427**, 356-364.
- 33 Y. Tanabe and S. Sugano, J. Phys. Soc. Jpn., 1954, 9, 753-766.
- 34 Q. Shao, H. Li, Y. Dong, J. Jiang, C. Liang and J. He, J. Alloy. Compd., 2010, 498, 199-202.
- 35 S. S. Wang, W. T. Chen, Y. Li, J. Wang, H. S. Sheu and R. S. Liu, J. Am. Chem. Soc., 2013, 135, 12504-12507.